

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

General Features

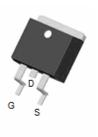
- V_{DS} =120V, I_D =190A $R_{DS(ON)}$ =3.0m Ω , typical (TO-220)@ V_{GS} =10V $R_{DS(ON)}$ =2.8m Ω , typical (TO-263)@ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

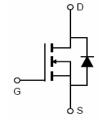
100% UIS TESTED! 100% ΔVds TESTED!

TO-220



TO-263





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP035N12	NCEP035N12	TO-220	-	-	-
NCEP035N12D	NCEP035N12D	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_c=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	120	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	190	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	135	Α
Pulsed Drain Current	I _{DM}	760	Α
Maximum Power Dissipation	P _D	300	W
Derating factor		2	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	2300	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{ heta JC}$	0.5	°C/W
,			1



Electrical Characteristics (T_C=25 ℃ unless otherwise noted)

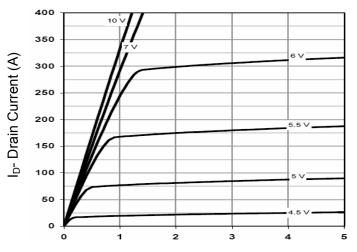
Parameter	Symbol	Condition		Min	Тур	Max	Unit
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA		120		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =120V,V _{GS} =0V		-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V		-	-	±100	nA
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=2$	250μA	2.0	3.0	4.0	V
Drain Course On State Besistance	Б	V _{GS} =10V, I _D =95A	TO-220	-	3.0	3.5	mΩ
Drain-Source On-State Resistance	$R_{DS(ON)}$		TO-263		2.8	3.5	mΩ
Forward Transconductance	g FS	$V_{DS}=5V,I_{D}=5V$	95A		90	-	S
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	V _{DS} =60V,V _{GS} =0V, F=1.0MHz		-	12700	-	PF
Output Capacitance	Coss			-	870	-	PF
Reverse Transfer Capacitance	C _{rss}			-	48	-	PF
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}	V_{DD} =60V, I_{D} =95A V_{GS} =10V, R_{G} =1.6 Ω		-	34	-	nS
Turn-on Rise Time	t _r			-	27	-	nS
Turn-Off Delay Time	t _{d(off)}			-	78	-	nS
Turn-Off Fall Time	t _f			-	30	-	nS
Total Gate Charge	Qg	V _{DS} =50V,I _D =95A, V _{GS} =10V		-	213	-	nC
Gate-Source Charge	Q_{gs}			-	58		nC
Gate-Drain Charge	Q_{gd}			-	58		nC
Drain-Source Diode Characteristics						'	
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =95A		-		1.2	V
Diode Forward Current (Note 2)	Is			-	-	190	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 100A		-	101	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)		-	280	-	nC

Notes:

- ${\bf 1.}\ {\bf Repetitive}\ {\bf Rating:}\ {\bf Pulse}\ {\bf width}\ {\bf limited}\ {\bf by}\ {\bf maximum}\ {\bf junction}\ {\bf temperature}.$
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=60V,VG=10V,L=0.5mH,Rg=25 Ω

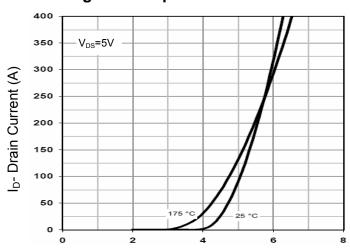


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

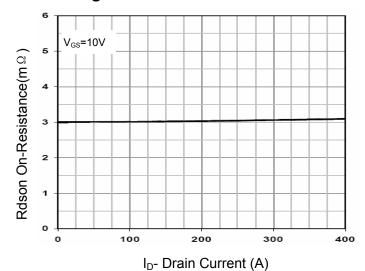
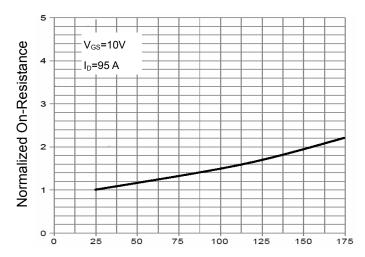
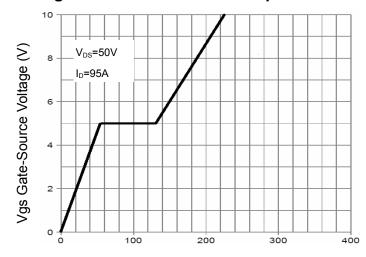


Figure 3 Rdson- Drain Current

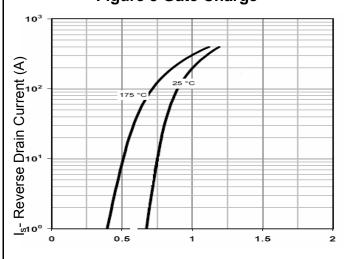


T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



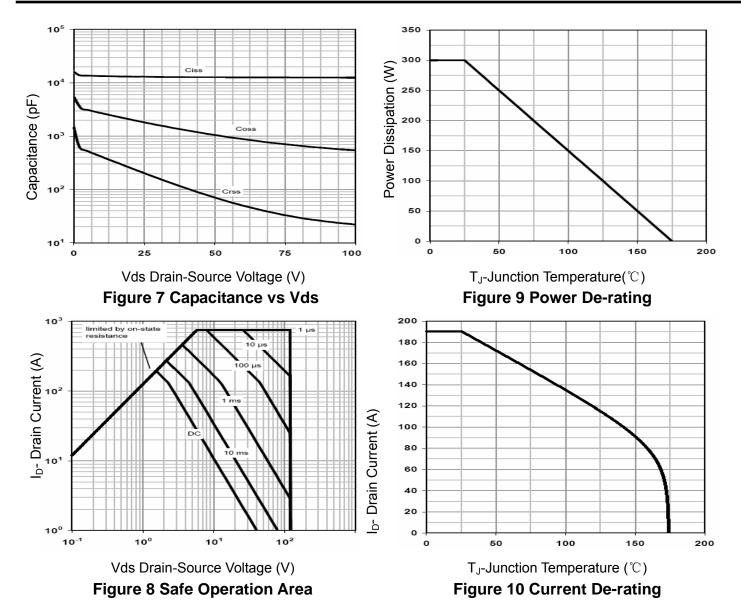
Qg Gate Charge (nC)
Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward





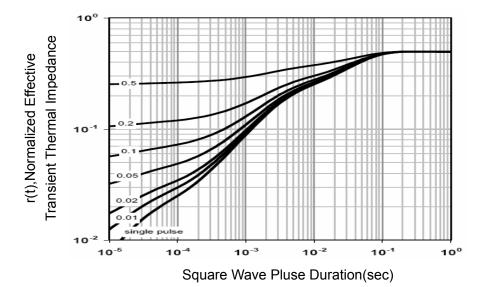
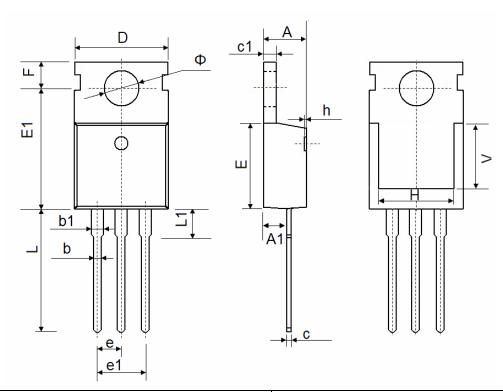


Figure 11 Normalized Maximum Transient Thermal Impedance



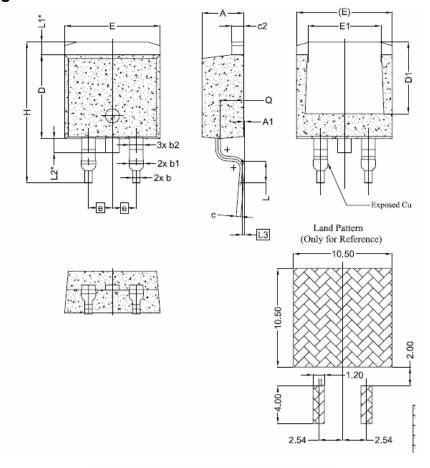
TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900 REF.		0.276 REF.		
Ф	3.400	3.800	0.134	0.150	



TO-263-2L Package Information



SYMBOL	DIMENSIONS				
STIMBOL	MIN.	NOM.	MAX.		
Α	4.24	4.44	4.64		
A1	0.00	0.10	0.25		
b	0.70	0.80	0.90		
b1	1.20	1,55	1.75		
b2	1,20	1,45	1,70		
С	0.40	0.50	0.60		
c2	1,15 1,27		1,40		
D	8.82 8.92		9.02		
D1	6.86 7.65		_		
E	9.96 10.16		10.36		
E1	6.89	7.77	7.89		
е	2,54 BSC				
Н	14,61 15,00		15,88		
L	1.78	2.32	2.79		
L1	1.36 REF.				
L2	1.50 REF.				
L3	0.25 BSC				
Q	2.30	2.48	2.70		



NCEP035N12,NCEP035N12D

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